AgFeS₂-Nanowire-Modified BiVO₄ Photoanodes for Photoelectrochemical Water Splitting

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Photoelectrochemical water splitting is a promising and environmentally friendly route for the conversion of solar energy into hydrogen. However, the efficiency of this energy conversion process is low because of the limited light absorption and rapid bulk recombination of charge carriers. In this study, the combination of a novel ternary sensitizer AgFeS₂, having a narrow bandgap of 0.9 eV, with a BiVO₄ electrode is presented for the enhancement of the solar-energy-to-hydrogen conversion efficiency. The photoelectrochemical properties of this

combined material were investigated and the photocurrent densities of $AgFeS_2$ -BiVO₄ composite electrodes were greatly enhanced compared with pristine BiVO₄ (15 times higher at 0.6 V vs. Ag/AgCl under AM 1.5G illumination). The enhanced photoelectrochemical properties arise from extended light absorption, fast charge transfer and appropriate energy gap alignment. It was demonstrated that AgFeS₂ nanowires are promising inorganic sensitizers for improving the efficiency of solar water splitting.

Introduction

Since the discovery of water splitting on titanium dioxide (TiO₂) surfaces by photoirradiation, photoelectrochemical (PEC) technology has attracted extensive interest.^[1] After decades of development, great progress has been made in the production of H₂ by water splitting, the degradation of organic pollutants and CO₂ reduction.^[2-5] However, the efficiency of such PEC processes is still low, which seriously restricts their wide application in solving energy shortage and environmental pollution problems. Investigating new and efficient photoelectrodes has been shown to be important for improving PEC efficiency and promoting the practical application of PEC technology. Among photoelectrode materials, bismuth vanadate (BiVO₄) is one of the leading metal oxides, with a direct bandgap of 2.3-2.4 eV and a suitable valence band position for O₂ evolution.^[6] BiVO₄ was first reported by Kudo and co-workers as a photocatalyst for water oxidation.^[7] Since then, BiVO₄ has been widely investigated as a visible-light-driven photocatalyst for water oxidation and organic compound degradation.[8-12] Recently, extensive attention has focused on BiVO4 as a photoanode for PEC water splitting.^[13-16] However, the activity of pure BiVO₄ is low

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Supporting information for this article can be found under http:// dx.doi.org/10.1002/cplu.201600095.

This article is part of a Special Issue on "Catalytic Systems for Water Splitting". To view the complete issue, visit: http://dx.doi.org/10.1002/cplu.v81.10.

due to its poor light absorption and difficult migration of electron-hole pairs, which has been demonstrated by van de Krol and co-workers.^[17] Therefore, poor electron transport results in high bulk recombination of photogenerated charge carriers and low solar-to-hydrogen energy conversion efficiency.

To address these issues, many attempts have been made to modify the bulk electronic properties of BiVO₄ photocatalysts, such as applying noble-metal coatings, elemental doping and combining narrow bandgap semiconductors.^[15, 18-23] Among these methods, one of the most efficient ways is to deposit a sensitizer with an appropriate band gap onto BiVO₄. The sensitizer not only extends the light absorption spectrum, but also accelerates photogenerated electron-hole separation. Ternary I-III-VI₂ semiconductors are regarded as one of the most promising materials for thin-film sensitizers because of their unique properties, large absorption coefficients, high conversion efficiency, and low toxicity.^[24] Silver iron sulfide (AgFeS₂, Lenaite) is a novel ternary I-III-VI₂ semiconductor, which has a narrow band gap (\approx 0.9 eV) covering the entire visible spectrum and also has a high absorption coefficient.[25] Sciacca et al. and Han et al. have obtained AgFeS₂ by different synthetic pathways.^[25,26] To the best of our knowledge, to date, there has been no report on PEC electrodes made from BiVO₄ modified with ternary AgFeS₂. This study extends the work to a new, coupled photoanode consisting of the ternary sensitizer AgFeS₂ and BiVO₄.

We prepared a $AgFeS_2$ -BiVO₄ composite by incorporating $AgFeS_2$ with a $BiVO_4$ film by means of a simple drop-coating method. The composite of $AgFeS_2$ and $BiVO_4$ semiconductors with appropriate oxidation-reduction energy levels enhanced the charge separation and generated a wide spectral response by extension of light absorption in the visible region. In this study, ternary $AgFeS_2$ -modified $BiVO_4$ is fabricated on a fluo-rine-doped tin oxide (FTO) substrate and applied as a photoa-



node. The expected enhanced PEC properties of $AgFeS_2$ -BiVO₄ composite were confirmed by hydrogen and oxygen evolution from solar water splitting. The mechanism for the enhanced PEC performance and gas evolution on the $AgFeS_2$ -BiVO₄ composite is discussed in detail.

Results and Discussion

Fabrication and characterization of $\mathsf{AgFeS}_2\text{-}\mathsf{BiVO}_4$ composite electrodes

Scanning electron microscopy (SEM) was used to investigate the morphology of the as-prepared $AgFeS_2$, $BiVO_4$ and $AgFeS_2$ – $BiVO_4$ samples (Figure 1). Figure 1 a shows the typical morphol-



Figure 1. SEM images of a) AgFeS₂ nanowires and b) AB-40 composite.

ogy of AgFeS₂. It is comprised of nanowires approximately 10 μ m in length. The morphology of the BiVO₄ (Figure S1 in the Supporting information) was also investigated, and was found to comprise nanoparticles with diameters from 100 to 400 nm. AgFeS₂ nanowires were firstly prepared by a solutionphase conversion of metallic Ag nanowires described in our previous report.^[25] The as-prepared AgFeS₂ nanowires were then stirred in ethanol for 24 h to form a suspension, which was dropped onto the BiVO₄ film to obtain the AgFeS₂-BiVO₄ composite. According to the amount of AgFeS₂ (10, 20, 30, 40 and 50 μ L) being added on the BiVO₄ samples, the corresponding AgFeS₂-BiVO₄ samples were designated AB-10, AB-20, AB-30, AB-40 and AB-50, respectively. As the morphologies of AgFeS₂-BiVO₄ samples containing different amounts of AgFeS₂ are almost the same, only the coverage of $AgFeS_2$ on $BiVO_4$ is different. The photocurrent density of the AB-40 electrode is higher than other AgFeS₂-BiVO₄ samples, therefore it was chosen as the example composite for the SEM and energy-dispersive X-ray (EDX) measurements. For the AB-40 sample, it was clearly observed that AgFeS₂ nanowires are on the top surface of BiVO₄ (Figure 1b and Figure S2). Furthermore, EDX mapping obtained in the SEM mode (Figure 2) was performed to confirm the composition of AB-40. As seen from the SEM image (Figure 2a), the AgFeS₂ nanowires are crystalline, which was confirmed by electron diffraction in our previous synthetic study. $^{\left[25\right] }$ Moreover, the elements Ag, Fe, and S (Figure 2 b–d) are distributed homogeneously along the nanowires, indicating the existence of AgFeS₂. The elements Bi, V and O (Figure 2e-g) were also detected, which are associated with the



1µm



Figure 2. SEM and EDX characterization of AB-40 sample: a) high-magnification SEM image; b–g) element mapping of Ag, Fe, S, Bi, V and O, respectively.

 $BiVO_4$ substrate. The composite structure of AgFeS₂-BiVO₄ was thus confirmed by the SEM and EDX results.

The crystal structures of BiVO₄ and AB-40 were determined by x-ray diffraction (XRD), as shown in Figure 3. The XRD pattern of BiVO₄ can be matched to monoclinic BiVO₄ (JCPDS No. 14-0688); the FTO film (JCPDS No. 41-1445) is shown in Figure S3. The 2 θ diffraction peaks of 28.8°, 30.5°, 34.5°, 35.2°, 39.8°, and 42.5° can be respectively indexed as the (121), (040),



Figure 3. XRD patterns of BiVO₄ and AB-40.



(200), (002), (211), and (051) planes of the monoclinic BiVO₄ structure, which is consistent with the literature.^[27] The 2 θ diffraction peaks and corresponding planes of AgFeS₂ (JCPDS No. 48-1895) are shown in Figure S4. Notably, AgFeS₂ is clearly apparent in the XRD pattern of the AB-40 sample. Based on the results of SEM images, elemental mapping and XRD patterns, it is clear that the AgFeS₂–BiVO₄ composite was successfully prepared using a simple drop-coating approach.

It is well known that light absorption of the photoelectrode material plays an important role in solar water splitting. The UV/Vis diffuse reflection spectra of BiVO₄, AgFeS₂, and AgFeS₂–BiVO₄ composites with different AgFeS₂ content were thus measured. The optical bandgap energy (*E*_g) of BiVO₄ (Figure S5) was obtained by using the equation $[F(R)E]^{1/2} = A(E - E_g)$.^[28] where *E* is the energy of a photon and *A* is a constant. The estimated bandgap value of BiVO₄ as a direct band semiconductor is 2.32 eV, which is in agreement with previously reported values.^[7,8] From a further analysis of the diffuse reflection spectra (Figure 4), it is apparent that there are enhancements in



Figure 4. UV/Vis diffuse reflectance spectra of $AgFeS_2$, $BiVO_4$ and $AgFeS_2$ - $BiVO_4$ composites with different $AgFeS_2$ contents.

the light absorption of $AgFeS_2$ -BiVO₄ composites compared with the bare BiVO₄. This is due to the fact that $AgFeS_2$, having a narrow band gap (0.88 eV), significantly extends the light absorption range of $AgFeS_2$ -BiVO₄ composites. With the introduction of $AgFeS_2$, a more efficient utilization of the solar spectrum on $AgFeS_2$ -BiVO₄ can be achieved, which is helpful to improve the PEC properties and facilitates its use in practical solar water splitting. The $AgFeS_2$ -FTO film was prepared by adding a $AgFeS_2$ suspension onto FTO until fully covering the surface. Therefore, the amount of $AgFeS_2$ on the FTO substrate is higher than the other samples; this is the reason that $AgFeS_2$ film has much lower R% (reflectance).

Photoelectrochemical properties of AgFeS2-BiVO4 electrodes

The photocurrent densities as a function of applied potential of $AgFeS_2$, $BiVO_4$ and $AgFeS_2$ - $BiVO_4$ electrodes were investigated by linear sweep photovoltammetry (LSV), which measured

their electron generation capacity and electron transfer efficiency. The photocurrent responses of AgFeS₂, BiVO₄ and AgFeS₂-BiVO₄ photoelectrodes (Figure 5) were studied under AM 1.5G illumination (100 mW cm⁻²). Figure 5 a shows LSV (scan rate 10 mV s⁻¹) of the BiVO₄, AgFeS₂ and AgFeS₂-BiVO₄ photoanodes under illumination from the backside (FTO side) of the electrodes. The anodic photocurrents increased steadily with the applied positive potential, and an enhanced photocurrent for the AgFeS2-BiVO4 composite electrodes was obtained essentially over the entire potential range compared with BiVO₄ electrode. The AB-40 electrode showed the greatest enhancement of all of the electrodes, and the current in the dark was negligible. This significant improvement in photocurrent could be attributed to the effect of AgFeS₂ modification. It is also notable that pristine AgFeS₂ shows a low photocurrent. The linear sweep voltammograms of the photoanodes under chopped illumination were also studied and showed a similar trend (Figure 5 b). The BiVO₄ photoanode demonstrated a low photocurrent that is indeed lower than most of the values reported in the literature on BiVO₄ photoelectrodes.^[29,30] The poor PEC performance is mainly caused by non-uniform distribution of the BiVO₄ nanoparticles on the FTO surface, which is not fully covered by BiVO4 nanoparticles. It was thus anticipated that the photocurrent of the AgFeS2-BiVO4 composite



Figure 5. Photocurrent generation versus bias potential (vs. Ag/AgCl) obtained from AgFeS₂, BiVO₄ and AgFeS₂–BiVO₄ composites a) without chopped illumination and b) under chopped AM 1.5G illumination (100 mW cm⁻²) in 0.1 \times Na₂SO₄.



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would be much higher if a ${\rm BiVO}_4$ substrate of better quality was used.

Additional PEC measurements (Figure 6) were performed to further investigate the enhancement mechanism for water splitting at the AgFeS₂-BiVO₄ composite electrode. Figure 6a shows the photocurrent versus time curves (0.6 V vs. Aq/AqCl under AM 1.5G illumination) for the samples with several onoff cycles. The photocurrent responses of the AgFeS₂-BiVO₄ composite films were higher than those of $BiVO_4$ and $AgFeS_2$, and AB-40 demonstrated the highest photocurrent among them, which was almost 15 times higher than that of BiVO₄. As shown in Figure 6b, it is clear that the radius of the arc on the electrochemical impedance spectroscopy (EIS) Nyquist plots of AgFeS₂-BiVO₄ samples are smaller than that of BiVO₄, which is consistent with AgFeS₂-BiVO₄ favoring faster interfacial charge transfer. The results are in good agreement with the photocurrent measurements. According to the photocurrent curves and EIS plots, the presence of AgFeS₂ in the AgFeS₂-BiVO₄ composite is capable of improving separation efficiency and effectively inhibiting the recombination of photogenerated electronhole pairs. Such an explanation would also make more sense given its small bandgap, which means it should not participate directly in water splitting.

To further gain a qualitative understanding of the charge recombination behavior in BiVO₄ and AB-40, the transient photocurrent decay occurring immediately upon illumination was investigated (Figure 6 c). Measuring the transient photocurrent response has been demonstrated to be a useful technique for investigating the efficiency of the separation of photogenerated electron-hole pairs.^[31] The photocurrent curve initially presents a spike, which gradually decays until the photocurrent reaches a stable value. The decrease in the photocurrent indicates that recombination occurs within the $AgFeS_2$ -BiVO₄ electrode. If the incident light is switched on, a photocurrent spike is observed at an applied potential of 0.6 V versus Ag/AgCl due to the sudden generation of charge carriers, which then recombine. Charge recombination can be caused either by accumulation of electrons in the bulk or accumulation of holes at the surface. The accumulation of holes would cause an equally large cathodic transient if the light is switched off and electrons in the conduction band react with the accumulated holes.^[9] However, cathodic transients were barely observed, indicating that accumulation of holes is not the main recombination process in BiVO₄ film and AB-40 electrodes. The transients shown in Figure 6c are thus attributed to the accumulation of electrons due to the poor electron transport in BiVO₄, which is



Figure 6. a) Photocurrent spectra and b) EIS Nyquist plots of AgFeS₂, BiVO₄ and AgFeS₂–BiVO₄ with an applied bias potential of 0.6 V vs. Ag/AgCl under AM 1.5G illumination (100 mW cm⁻²). c) Transient photocurrent decay and d) transient decay times of BiVO₄ film and AB-40 electrodes (see text for the definition of parameter *D*).



consistent with results observed previously.^[14] The transient decay time can be calculated from a logarithmic plot of parameter *D*, given by Equation (1):^[32, 33]

$$D = (I_t - I_s) / (I_m - I_s)$$
(1)

where I_m is the maximum photocurrent of the spike, I_t is the photocurrent at time t and I_s is the steady-state photocurrent. Is is achieved as the recombination and charge generation reaches equilibrium. The transient decay time is defined as the time at which $\ln D = -1$.^[32] Therefore, based on the photocurrent profiles (Figure 6 c), the transient decay times of BiVO₄ film and AB-40 electrodes were calculated and are plotted in Figure 6 d. The transient decay time for AB-40 electrode was 1.87 s, which is more than three times longer than the transient decay time of BiVO₄ film (0.49 s). In general, the photocurrent decay rate is determined by the charge carrier recombination rate.^[33] Therefore, we expect that a slower recombination rate gives rise to a longer transient decay time. Indeed, a significantly longer transient decay time was observed for the AB-40, suggesting a lower charge carrier recombination rate in AB-40 compared to the BiVO₄ film.

In order to address the quantitative correlation between AgFeS₂ sensitization and light absorption of AgFeS₂–BiVO₄ composites, incident-photon-to-current-conversion efficiency (IPCE) measurements were performed to study the photoactive wavelength regime for AgFeS₂, BiVO₄ and AB-40 (Figure 7). IPCE can be expressed as Equation (2):^[34,35]

$$IPCE = (1240 \times I) / (\lambda \times J_{light})$$
⁽²⁾

where *I* is the photocurrent density, λ is the wavelength of the incident light, and J_{light} is the measured irradiance. For AgFeS₂ itself, the IPCE data is low, which is consistent with the photocurrent data. The IPCE plots of BiVO₄ and AB-40 look similar and strongly decrease upon excitation at longer wavelengths; the BiVO₄ showed a minimal photoresponse below the bandgap energy ($\approx 2.32 \text{ eV}$, 535 nm), whereas the composite electrode (AB-40) showed a significant redshift toward lower



Figure 7. Measured IPCE spectra of AgFeS₂, BiVO₄ and AB-40 in the region 400–800 nm at a potential of +0.6 V under AM 1.5G illumination (100 mW cm⁻²).

energy. For example, at above-bandgap illumination, the IPCE of pure $BiVO_4$ and AB-40 samples at the incident wavelength of 500 nm are 1.03% and 6.59%, respectively, indicating that the presence of AgFeS₂ can improve the charge separation efficiency and thus give an enhanced photoresponse. At below-bandgap illumination of 550 nm, the IPCE of AB-40 is around 5%, while pristine $BiVO_4$ shows no photoresponse. This is direct evidence that AgFeS₂ can also act as a photosensitizer and substantially improves the light collection and conversion efficiency in the visible region.

To verify that the measured photocurrent of the photoanodes originated from water splitting and not undesired side reactions, a water splitting experiment was performed at 1.6 V on the AB-40 photoanode, and the gas evolution (Figure 8)



Figure 8. Gas evolution of the AB-40 photoanode at an applied potential of 1.6 V (vs. Ag/AgCl) under AM 1.5G illumination (100 mW cm⁻²).

and corresponding photocurrent response (Figure S6) were measured. The ratio of evolution rates of H₂ and O₂ is close to the stoichiometric value of 2.0, with rates of $9.1\pm$ 0.1 µmol h⁻¹ cm⁻² for H₂ and 4.3 ± 0.1 µmol h⁻¹ cm⁻² for O₂. By assuming 100% faradaic efficiency, at a photocurrent of 0.60 mA cm⁻², the evolution rates of H₂ and O₂ should be 10.6 and 5.3 µmol h⁻¹ cm⁻², respectively. Hence the faradaic efficiencies for H₂ and O₂ are more than 80%, indicating that the observed photocurrent could be mostly attributed to water splitting. Additionally, the photocurrent of AB-40 only slightly decreases after 3 h of the water splitting experiment (Figure S6), implying the high stability of the AgFeS₂–BiVO₄ composite photoanode. It can be concluded that AgFeS₂ is relatively stable and promising as a sensitizer for solar water splitting.

Photoelectrochemical mechanism for water splitting at the AgFeS₂-BiVO₄ composite photoanode

Based on the above data, a possible mechanism for the water splitting at the $AgFeS_2$ -BiVO₄ composite photoanode under light irradiation can be proposed. Here $AgFeS_2$ serves as a sensitizer for light-induced redox process and BiVO₄ is a substrate. The bandgap of BiVO₄ was evaluated as 2.32 eV from the UV/ Vis spectrum, which is consistent with literature reports.^[7,8] The



corresponding conduction band (E_{CB}) and valence band (E_{VB}) positions of BiVO₄ and AgFeS₂ at the point of zero charge were presumed according to the following equations [Eqs. (3) and (4)]:^[36,37]

$$\chi = 1/2(A_{\rm f} + I_1) \tag{3}$$

$$E_{\rm CB} = \chi - E_0 - 1/2 E_{\rm g} \tag{4}$$

where χ is the bulk electronegativity of the compound, defined as the arithmetic mean of the atomic electron affinity and the first ionization energy (for BiVO4, χ is 6.04 eV;^[37,38] for AgFeS₂, χ is 5.14 eV^[36]). A_f and I_1 are the atomic electron affinity and the first ionization potential, respectively. E_0 is the energy of free electrons on the hydrogen scale (about 4.5 eV), and E_g is the bandgap energy of the semiconductor. The position of the valence band edge is determined by $E_{VB} = E_{CB} + E_g$. The calculated result shows that the bottom of the conduction band of BiVO₄ is around 0.4 eV versus the normal hydrogen electrode (NHE), whereas the top of the valence band is around 2.7 eV. The value of E_{CB} measured (Figure S7) by photocurrent onset potential is in accordance with the calculated result. The calculated conduction band and valence band positions (vs. NHE) of AgFeS₂ and BiVO₄ are listed in Table 1.

The energy band diagram of the AgFeS₂–BiVO₄ composite photoanode is presented in Figure 9. The difference in E_{CB} between AgFeS₂ and BiVO₄ allows for the transfer of electrons from the conduction band of AgFeS₂ to that of BiVO₄. Upon light irradiation ($\lambda < 535$ nm), both the AgFeS₂ and BiVO₄ components generate electron–hole pairs, although the majority are from the BiVO₄ due to its large excess. Whereas the electrons are able to move easily to the FTO contact site, the holes are expected to remain on the surface of AgFeS₂–BiVO₄ photoanode. This improved charge separation efficiency leads to improved water oxidation. Conversely, under light irradiation Table 1. Absolute electronegativity, energy band gap, calculated conduction band (CB) edge and valance band (VB) edge versus normal hydrogen electrode (NHE) at the point of zero charge for $AgFeS_2$ and $BiVO_4$ semiconductors.

Semiconductor	Abs. electro-	Calcd CB	Calcd VB	Energy band
	neg. (χ) [eV]	edge [eV]	edge [eV]	gap <i>E</i> g [eV]
AgFeS ₂	5.14	0.04	0.92	0.88
BiVO ₄	6.04	0.38	2.70	2.32

beyond the absorption edge of BiVO₄ (λ > 535 nm), the electrons photogenerated in AgFeS₂ due to its small band gap can readily transfer to the conduction band of BiVO4, which improves the charge carrier separation in AgFeS₂. AgFeS₂ itself is unable to directly split water toward O₂ due to the unfavorable position of the valence band with respect to the O₂/H₂O redox potential. However, the holes trapped at the AgFeS₂ component can react with H_2O to form OH radicals $(H_2O + h^+ \rightarrow OH^+ +$ H⁺).^[39] OH radicals are highly reactive and, in the absence of other species, can couple with another OH radical to form H_2O_2 (2 OH $\rightarrow H_2O_2$).^[40] Hydrogen peroxide is known to decompose spontaneously to O_2 and water, and H_2O_2 can also be photo-oxidized by holes in BiVO₄ $(H_2O_2 + h^+ \rightarrow O_2 + H^+ +$ $4\,e^{-}).^{[41-43]}$ Overall, photogenerated holes formed in both $BiVO_4$ and AgFeS₂, follow different pathways to react with water to form O₂. As a consequence, a higher number of collected photo electrons are formed $^{\rm [44,45]}$, which are then used for the $\rm H_2$ production in the cathodic electrode.

Conclusion

Photoelectrodes made of $AgFeS_2$ -nanowire-BiVO₄ composites were fabricated by using a facile drop-coating method. $AgFeS_2$ nanowires, with a narrow band gap of 0.9 eV, were demon-



Figure 9. Mechanism of UV/Vis light absorption and charge transfer in AgFeS₂-BiVO₄ composite films for the PEC water splitting reaction.



strated as novel ternary sensitizers for improving the water splitting efficiency of a BiVO4 photoanode. The photocurrent density of AgFeS₂-BiVO₄ electrode was greatly enhanced compared with pristine BiVO₄ electrode (15 times higher at 0.6 V vs. Ag/AgCl under AM 1.5G illumination). The excellent PEC properties arise from the extended light absorption spectrum and improved charge separation and collection efficiency. Furthermore, hydrogen and oxygen production on AgFeS₂-BiVO₄ electrodes was measured and these composite photoelectrodes were found to be promising for solar water splitting. AgFeS₂ drastically improves the solar water splitting efficiency of BiVO₄ photoanodes, suggesting AgFeS₂ as a new effective sensitizer for improving the efficiency of solar-to-fuel energy conversion. Further work to prepare a more active BiVO₄ substrate and more stable AgFeS₂ by surface modification is being conducted in our laboratory.

Experimental Section

Preparation of the AgFeS₂-BiVO₄ composite

The AgFeS₂ nanowires were obtained by using a modified synthesis from our previous report, optimized for larger scale reactions with higher yield.^[25] In a typical reaction, DMSO (90 mL) was placed in a round-bottom flask and FeCl₂·4H₂O (102 mg), thioglycolic acid (100 μ L) and Ag nanowire solution (20 g L⁻¹, 2.5 mL) were added. N₂ was bubbled through the solution for 30 min to remove oxygen. Subsequently, a solution of Na₂S₂O₃·5H₂O (451 mg) in water (10 mL) purged with N₂ was slowly added to the rest of the reagents over approximately 30 min. The color of the solution was dark purple at this stage. The flask was then placed in an oil bath at 150 °C and heated at reflux for 90 min. The solution was then allowed to cool to room temperature, centrifuged (200 g, 5 min) and washed several times in water and ethanol to remove DMSO and unreacted species. The sample was then dispersed in ethanol. A pellet of the sample was then obtained by evaporating the solvent at 50 °C.

To synthesize BiVO₄, Bi(NO₃)₃·5 H₂O (0.5 mmol) and NH₄VO₃ (0.5 mmol) were dissolved in nitric acid (5 mL) and distilled water (5 mL). The mixed solution (2×20 μ L) was dropped onto the FTO surface of 1×1 cm area. After being dried, the film was calcined at 500 °C for 2 h with a ramping rate of 2 °C min⁻¹.

The AgFeS₂–BiVO₄ composites were prepared by dropping a suspension of AgFeS₂ onto the BiVO₄ film. Firstly, AgFeS₂ (4 mg) was added to ethanol (200 µL) with constant stirring. After being stirred for 24 h, the AgFeS₂ suspension was dropped onto the BiVO₄ film. The volume of AgFeS₂ suspension added was 10, 20, 30, 40 and 50 µL, and the corresponding AgFeS₂–BiVO₄ samples were labeled AB-10, AB-20, AB-30, AB-40 and AB-50, respectively. The AgFeS₂–FTO film was prepared by adding AgFeS₂ suspension onto a FTO film until it was fully covered.

Characterization of samples

The XRD patterns were measured on a Bruker D8 Advance X-ray diffractometer with CuK α radiation. The accelerating voltage and applied current were 40 kV and 40 mA, respectively. UV/Vis diffuse reflectance spectra of samples were collected using an UV/Vis/NIR spectrometer (UV-2600, Shimadzu co., Japan) with BaSO₄ as the background in the range 200–800 nm. The general morphologies

and element mapping of the products were examined by field emission scanning electron microscopy (FESEM) on a Sigma Zeiss 150 instrument (Carl Zeiss, Oberkochen, Germany) operated at 5 kV. The PEC data was collected on a CHI-660E electrochemical workstation (Chenhua Instruments, Co., Shanghai, China). The PEC experiment was performed in a conventional three-electrode system with a quartz cell. A Pt wire and an Ag/AgCl electrode were used as counter and reference electrodes, respectively. The electrolyte was Na₂SO₄ (0.1 m) solution.

Photoelectrochemical measurements

The PEC characterization was performed with the CHI-660E electrochemical workstation under illumination by a 300 W Xe lamp (CEL-S500, Beijing Jin Yuan Science and Technology Co., Beijing, China) equipped with the AM 1.5G filter (light intensity: 100 mW cm⁻²). The incident-photon-to-current-conversion efficiency (IPCE) was measured by interposing a monochromator (7ISW15, Beijing 7-Star Optical Instruments Co., Beijing, China) between the xenon lamp and the PEC cell. The monochromatic light was passed through filter plates for different wavelengths with a bandwidth of 10 nm, and the monochromatic light power density was measured with a UV/Vis irradiatometer (CEL-NP2000, Beijing Jin Yuan science and Technology Co.) with an accuracy of 1 μ W cm⁻².

Acknowledgements

We gratefully acknowledge financial support from the National Nature Science Foundation of China (No. 21507011), the Eastern Scholar Program (SSH1829002) and the Thousand Young Talents Program to L.Z.. This study is part of the research program of the Foundation for Fundamental Research on Matter (FOM), which is part of the Netherlands Organization for Scientific Research (NOW). We acknowledge financial support from the European Research Council under the European Union's Seventh Framework Programme (FP/2007-2013)/ERC Grant Agreement no. 337328, "NanoEnabledPV".

Keywords: composite materials • extended light absorption • photoelectrochemistry • sensitizers • water splitting

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Manuscript received: March 16, 2016 Accepted Article published: April 28, 2016 Final Article published: May 30, 2016